

# Qian Sun ??

## List of Publications by Year in Descending Order

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131  
papers

2,629  
citations

29  
h-index

46  
g-index

142  
ext. papers

3,088  
ext. citations

3.6  
avg, IF

4.79  
L-index

#	Paper	IF	Citations
131	GaN-based distributed feedback laser diodes grown on Si. <i>Journal Physics D: Applied Physics</i> , <b>2022</b> , 55, 195103	3	
130	Electrically injected GaN-on-Si blue microdisk laser diodes.. <i>Optics Express</i> , <b>2022</b> , 30, 13039-13046	3.3	1
129	Narrow-Linewidth GaN-on-Si Laser Diode with Slot Gratings. <i>Nanomaterials</i> , <b>2021</b> , 11,	5.4	2
128	Identification of Semi-ON-state Current Collapse in AlGaIn/GaN HEMTs by Drain Current Deep Level Transient Spectroscopy. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 1-1	4.4	1
127	An ultrathin-barrier AlGaIn/GaN heterostructure: a recess-free technology for the fabrication and integration of GaN-based power devices and power-driven circuits. <i>Semiconductor Science and Technology</i> , <b>2021</b> , 36, 044002	1.8	1
126	High-Voltage and High-ION/IOFF Quasi-Vertical GaN-on-Si Schottky Barrier Diode With Argon-Implanted Termination. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 42, 473-476	4.4	17
125	Transfer-printed, tandem microscale light-emitting diodes for full-color displays. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , <b>2021</b> , 118,	11.5	7
124	Structure and luminescence of a-plane GaN on r-plane sapphire substrate modified by Si implantation*. <i>Chinese Physics B</i> , <b>2021</b> , 30, 056104	1.2	
123	III-nitride semiconductor lasers grown on Si. <i>Progress in Quantum Electronics</i> , <b>2021</b> , 77, 100323	9.1	13
122	Reverse leakage and breakdown mechanisms of vertical GaN-on-Si Schottky barrier diodes with and without implanted termination. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 243501	3.4	8
121	Gate Reliability and its Degradation Mechanism in the Normally OFF High-Electron-Mobility Transistors With Regrown p-GaN Gate. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , <b>2021</b> , 9, 3715-3724	5.6	5
120	Interface Charge Effects on 2-D Electron Gas in Vertical-Scaled Ultrathin-Barrier AlGaIn/GaN Heterostructure. <i>IEEE Transactions on Electron Devices</i> , <b>2021</b> , 68, 36-41	2.9	3
119	Influence of the carrier behaviors in p-GaN gate on the threshold voltage instability in the normally off high electron mobility transistor. <i>Applied Physics Letters</i> , <b>2021</b> , 119, 063501	3.4	7
118	Influence of traps on the gate reverse characteristics of normally-off high-electron-mobility transistors with regrown p-GaN gate. <i>Applied Physics Express</i> , <b>2021</b> , 14, 104005	2.4	0
117	Effect of Si Doping on the Performance of GaN Schottky Barrier Ultraviolet Photodetector Grown on Si Substrate. <i>Photonics</i> , <b>2021</b> , 8, 28	2.2	2
116	Nitrogen-Implanted Guard Rings for 600-V Quasi-Vertical GaN-on-Si Schottky Barrier Diodes With a BFOM of 0.26 GW/cm <sup>2</sup> <i>IEEE Transactions on Electron Devices</i> , <b>2021</b> , 1-5	2.9	7
115	GaN-Based Resonant-Cavity Light-Emitting Diodes Grown on Si.. <i>Nanomaterials</i> , <b>2021</b> , 12,	5.4	1

114	Effect of surface stoichiometry on the non-alloyed ohmic contact to N-face n-GaN. <i>Solid-State Electronics</i> , <b>2020</b> , 171, 107863	1.7	3
113	Thermal characterization of electrically injected GaN-based microdisk lasers on Si. <i>Applied Physics Express</i> , <b>2020</b> , 13, 074002	2.4	4
112	A p-GaN-Gated Hybrid Anode Lateral Diode with a Thicker AlGaN Barrier Layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2020</b> , 217, 1900781	1.6	4
111	AlGaN-based Schottky barrier deep ultraviolet photodetector grown on Si substrate. <i>Optics Express</i> , <b>2020</b> , 28, 17188-17195	3.3	16
110	Continuous-wave electrically injected GaN-on-Si microdisk laser diodes. <i>Optics Express</i> , <b>2020</b> , 28, 12201-12208	3.3	9
109	Enhanced carrier confinement and radiative recombination in GaN-based lasers by tailoring first-barrier doping. <i>Optics Express</i> , <b>2020</b> , 28, 32124-32131	3.3	3
108	Determination of carbon-related trap energy level in (Al)GaN buffers for high electron mobility transistors through a room-temperature approach. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 263501	3.4	10
107	Crack-free high quality 2 $\mu$ m-thick Al <sub>0.5</sub> Ga <sub>0.5</sub> N grown on a Si substrate with a superlattice transition layer. <i>CrystEngComm</i> , <b>2020</b> , 22, 1160-1165	3.3	7
106	InGaN-Based Lasers with an Inverted Ridge Waveguide Heterogeneously Integrated on Si(100). <i>ACS Photonics</i> , <b>2020</b> , 7, 2636-2642	6.3	2
105	Degradation study of InGaN-based laser diodes grown on Si. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 395103	3	2
104	Self-terminated Gate Recessing with a Low Density of Interface States and High Uniformity for Enhancement-mode GaN HEMTs <b>2020</b> ,		1
103	A wireless, implantable optoelectrochemical probe for optogenetic stimulation and dopamine detection. <i>Microsystems and Nanoengineering</i> , <b>2020</b> , 6, 64	7.7	29
102	Fabrication of AlGaN nanostructures by nanolithography on ultraviolet LEDs grown on Si substrates. <i>Nanotechnology</i> , <b>2019</b> , 30, 185201	3.4	4
101	Effect of Thermal Cleaning Prior to p-GaN Gate Regrowth for Normally Off High-Electron-Mobility Transistors. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 21982-21987	9.5	15
100	A fixed cytometer chip for identification of cell populations and real-time monitoring of single-cell apoptosis under gradient UV radiation. <i>Microfluidics and Nanofluidics</i> , <b>2019</b> , 23, 1	2.8	1
99	The abnormal aging phenomena in GaN-based near-ultraviolet laser diodes. <i>Journal Physics D: Applied Physics</i> , <b>2019</b> , 52, 275104	3	2
98	Recovery of p-GaN surface damage induced by dry etching for the formation of p-type Ohmic contact. <i>Applied Physics Express</i> , <b>2019</b> , 12, 055507	2.4	13
97	Improving the Current Spreading by Locally Modulating the Doping Type in the n-AlGaN Layer for AlGaN-Based Deep Ultraviolet Light-Emitting Diodes. <i>Nanoscale Research Letters</i> , <b>2019</b> , 14, 268	5	3

96	Normally-off HEMTs With Regrown p-GaN Gate and Low-Pressure Chemical Vapor Deposition SiNx Passivation by Using an AlN Pre-Layer. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 1495-1498	4.4	27
95	InGaN-Based Quantum Well Superluminescent Diode Monolithically Grown on Si. <i>ACS Photonics</i> , <b>2019</b> , 6, 2104-2109	6.3	5
94	Wafer-scale crack-free 10 $\mu$ m-thick GaN with a dislocation density of $5.8 \times 10^7$ cm <sup>-2</sup> grown on Si. <i>Journal Physics D: Applied Physics</i> , <b>2019</b> , 52, 425102	3	9
93	Capture and emission mechanisms of defect states at interface between nitride semiconductor and gate oxides in GaN-based metal-oxide-semiconductor power transistors. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 164505	2.5	9
92	Performance improvement of InGaN-based laser grown on Si by suppressing point defects. <i>Optics Express</i> , <b>2019</b> , 27, 25943-25952	3.3	8
91	GaN-based ultraviolet microdisk laser diode grown on Si. <i>Photonics Research</i> , <b>2019</b> , 7, B32	6	20
90	Accurate surface band bending determination on Ga-polar n-type GaN films by fitting x-ray valence band photoemission spectrum. <i>AIP Advances</i> , <b>2019</b> , 9, 115106	1.5	6
89	Evidence of a strong perpendicular magnetic anisotropy in Au/Co/MgO/GaN heterostructures. <i>Nanoscale Advances</i> , <b>2019</b> , 1, 4466-4475	5.1	1
88	GaN LEDs on Si Substrate. <i>Solid State Lighting Technology and Application Series</i> , <b>2019</b> , 133-170	0.7	7
87	Monolithic integration of E/D-mode GaN MIS-HEMTs on ultrathin-barrier AlGaIn/GaN heterostructure on Si substrates. <i>Applied Physics Express</i> , <b>2019</b> , 12, 024001	2.4	13
86	Ultrathin-Barrier AlGaIn/GaN Heterostructure: A Recess-Free Technology for Manufacturing High-Performance GaN-on-Si Power Devices. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 207-214	2.9	61
85	Room-Temperature Electrically Injected AlGaIn-Based near-Ultraviolet Laser Grown on Si. <i>ACS Photonics</i> , <b>2018</b> , 5, 699-704	6.3	31
84	Light output improvement of GaN-based light-emitting diodes grown on Si (111) by a via-thin-film structure. <i>Journal of Semiconductors</i> , <b>2018</b> , 39, 044002	2.3	10
83	On-Chip Integration of GaN-Based Laser, Modulator, and Photodetector Grown on Si. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2018</b> , 24, 1-5	3.8	31
82	High $f_{T}$ AlGa(In)N/GaN HEMTs Grown on Si With a Low Gate Leakage and a High ON/OFF Current Ratio. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 576-579	4.4	16
81	Room-temperature electrically pumped InGaN-based microdisk laser grown on Si. <i>Optics Express</i> , <b>2018</b> , 26, 5043-5051	3.3	25
80	Catalytic growth of highly crystalline polyaniline by copper under ambient conditions. <i>CrystEngComm</i> , <b>2018</b> , 20, 5119-5122	3.3	1
79	Room-temperature continuous-wave electrically pumped InGaN/GaN quantum well blue laser diode directly grown on Si. <i>Light: Science and Applications</i> , <b>2018</b> , 7, 13	16.7	73

78	Suppression of unintentional carbon incorporation in AlGa <sub>N</sub> -based near-ultraviolet light-emitting diode grown on Si. <i>Journal of Nanophotonics</i> , <b>2018</b> , 12, 1	1.1	4
77	Unintentional incorporation of Ga in the nominal AlN spacer of AlInGa <sub>N</sub> /AlN/GaN Heterostructure. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 035102	3	6
76	On-wafer fabrication of cavity mirrors for InGa <sub>N</sub> -based laser diode grown on Si. <i>Scientific Reports</i> , <b>2018</b> , 8, 7922	4.9	28
75	Thermal degradation of InGa <sub>N</sub> /Ga <sub>N</sub> quantum wells in blue laser diode structure during the epitaxial growth <b>2017</b> ,		4
74	Efficiency improvement of GaN-on-silicon thin-film light-emitting diodes with optimized via-like n-electrodes. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 075009	1.8	6
73	Mechanism of leakage of ion-implantation isolated AlGa <sub>N</sub> /Ga <sub>N</sub> MIS-high electron mobility transistors on Si substrate. <i>Solid-State Electronics</i> , <b>2017</b> , 134, 39-45	1.7	4
72	A 30 Mbps in-plane full-duplex light communication using a monolithic Ga <sub>N</sub> photonic circuit. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 075002	1.8	8
71	Self-terminated etching of Ga <sub>N</sub> with a high selectivity over AlGa <sub>N</sub> under inductively coupled Cl <sub>2</sub> /N <sub>2</sub> /O <sub>2</sub> plasma with a low-energy ion bombardment. <i>Applied Surface Science</i> , <b>2017</b> , 420, 817-824	6.7	23
70	Highly linearly polarized white light emission from InGa <sub>N</sub> light-emitting diode with nanograting-integrated fluorescent ceramics. <i>Applied Physics Express</i> , <b>2017</b> , 10, 012101	2.4	6
69	A Study of Efficiency Droop Phenomenon in Ga <sub>N</sub> -Based Laser Diodes before Lasing. <i>Materials</i> , <b>2017</b> , 10,	3.5	7
68	p-Ga <sub>N</sub> Gate Enhancement-Mode HEMT Through a High Tolerance Self-Terminated Etching Process. <i>IEEE Journal of the Electron Devices Society</i> , <b>2017</b> , 5, 340-346	2.3	28
67	High-power AlGa <sub>N</sub> -based near-ultraviolet light-emitting diodes grown on Si(111). <i>Applied Physics Express</i> , <b>2017</b> , 10, 072101	2.4	15
66	a-Axis Ga <sub>N</sub> /AlN/AlGa <sub>N</sub> Core-Shell Heterojunction Microwires as Normally Off High Electron Mobility Transistors. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 41435-41442	9.5	10
65	UVA light-emitting diode grown on Si substrate with enhanced electron and hole injections. <i>Optics Letters</i> , <b>2017</b> , 42, 4533-4536	3	23
64	Room-temperature continuous-wave electrically injected InGa <sub>N</sub> -based laser directly grown on Si. <i>Nature Photonics</i> , <b>2016</b> , 10, 595-599	33.9	151
63	High Uniformity Normally-OFF Ga <sub>N</sub> MIS-HEMTs Fabricated on Ultra-Thin-Barrier AlGa <sub>N</sub> /Ga <sub>N</sub> Heterostructure. <i>IEEE Electron Device Letters</i> , <b>2016</b> , 37, 1617-1620	4.4	54
62	Studies on High-Voltage Ga <sub>N</sub> -on-Si MIS-HEMTs Using LPCVD Si <sub>3</sub> N <sub>4</sub> as Gate Dielectric and Passivation Layer. <i>IEEE Transactions on Electron Devices</i> , <b>2016</b> , 63, 731-738	2.9	68
61	Normally OFF Ga <sub>N</sub> -on-Si MIS-HEMTs Fabricated With LPCVD-Si <sub>x</sub> N <sub>y</sub> Passivation and High-Temperature Gate Recess. <i>IEEE Transactions on Electron Devices</i> , <b>2016</b> , 63, 614-619	2.9	60

60	Properties of AlN film grown on Si (111). <i>Journal of Crystal Growth</i> , <b>2016</b> , 435, 76-83	1.6	11
59	Effects of thickness on optical characteristics and strain distribution of thin-film GaN light-emitting diodes transferred to Si substrates. <i>Applied Physics Express</i> , <b>2016</b> , 9, 042101	2.4	5
58	Stress evolution in AlN and GaN grown on Si(111): experiments and theoretical modeling. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2016</b> , 27, 2004-2013	2.1	10
57	Effects of Thickness of a Low-Temperature Buffer and Impurity Incorporation on the Characteristics of Nitrogen-polar GaN. <i>Nanoscale Research Letters</i> , <b>2016</b> , 11, 509	5	4
56	AlGaIn/GaN metal-insulator-semiconductor high electron mobility transistors with reduced leakage current and enhanced breakdown voltage using aluminum ion implantation. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 013507	3.4	7
55	Investigation of InGaIn/GaN laser degradation based on luminescence properties. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 213107	2.5	11
54	Off-state electrical breakdown of AlGaIn/GaN/Ga(In)N HEMT heterostructure grown on Si(111). <i>AIP Advances</i> , <b>2016</b> , 6, 035308	1.5	19
53	Fabrication of normally-off AlGaIn/GaN metal-insulator-semiconductor high-electron-mobility transistors by photo-electrochemical gate recess etching in ionic liquid. <i>Applied Physics Express</i> , <b>2016</b> , 9, 084102	2.4	13
52	GaN-on-Si blue/white LEDs: epitaxy, chip, and package. <i>Journal of Semiconductors</i> , <b>2016</b> , 37, 044006	2.3	53
51	Strain relaxation and dislocation reduction in AlGaIn step-graded buffer for crack-free GaN on Si (111). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 437-441		43
50	High efficient GaN-based laser diodes with tunnel junction. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 043508	3.4	18
49	Performance Enhancement of GaN-Based Laser Diodes With Prestrained Growth. <i>IEEE Photonics Technology Letters</i> , <b>2013</b> , 25, 2401-2404	2.2	
48	Preparation of GaN-on-Si based thin-film flip-chip LEDs. <i>Journal of Semiconductors</i> , <b>2013</b> , 34, 053006	2.3	3
47	Mechanical properties of nanoporous GaN and its application for separation and transfer of GaN thin films. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2013</b> , 5, 11074-9	9.5	36
46	Effects of matrix layer composition on the structural and optical properties of self-organized InGaIn quantum dots. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 093105	2.5	12
45	Classification of stacking faults and dislocations observed in nonpolar a-plane GaN epilayers using transmission electron microscopy. <i>Applied Surface Science</i> , <b>2012</b> , 258, 2522-2528	6.7	24
44	Growth evolution and microstructural characterization of semipolar (112 2) GaN selectively grown on etched r-plane sapphire. <i>Journal of Crystal Growth</i> , <b>2012</b> , 341, 27-33	1.6	18
43	Using the kinetic Wulff plot to design and control nonpolar and semipolar GaN heteroepitaxy. <i>Semiconductor Science and Technology</i> , <b>2012</b> , 27, 024005	1.8	54

42	The Role of Growth-Pressure on the Determination of Anisotropy Properties in Nonpolar-m-Plane GaN. <i>ECS Journal of Solid State Science and Technology</i> , <b>2012</b> , 1, R50-R53	2	4
41	Optical emission characteristics of semipolar (1,1,̄2,2) GaN light-emitting diodes grown on m-sapphire and stripe-etched-r-sapphire. <i>Semiconductor Science and Technology</i> , <b>2012</b> , 27, 024016	1.8	9
40	Heteroepitaxy of Nonpolar and Semipolar GaN. <i>Springer Series in Materials Science</i> , <b>2012</b> , 1-27	0.9	6
39	Understanding and controlling heteroepitaxy with the kinetic Wulff plot: A case study with GaN. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 053517	2.5	66
38	Surface striation, anisotropic in-plane strain, and degree of polarization in nonpolar-m-plane GaN grown on SiC. <i>Journal Physics D: Applied Physics</i> , <b>2011</b> , 44, 375103	3	9
37	Growth of cubic InN on GaP(1 0 0) with GaN buffer by metalorganic chemical vapour deposition. <i>Journal Physics D: Applied Physics</i> , <b>2011</b> , 44, 285403	3	1
36	Role of nonradiative recombination centers and extended defects in nonpolar GaN on light emission efficiency. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 072104	3.4	30
35	The fabrication of large-area, free-standing GaN by a novel nanoetching process. <i>Nanotechnology</i> , <b>2011</b> , 22, 045603	3.4	48
34	Nonpolar and semipolar GaN heteroepitaxy on sapphire for LED application <b>2010</b> ,		2
33	a-plane GaN hydride vapor phase epitaxy on a-plane GaN templates with and without use of TiN intermediate layers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2010</b> , 28, 1039-1043	1.3	1
32	Surface and interface states of gallium-polar versus nitrogen-polar GaN: Impact of thin organic semiconductor overlayers. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 113707	2.5	16
31	Electrical and luminescent properties and deep traps spectra of N-polar GaN films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2010</b> , 166, 83-88	3.1	9
30	Electrical properties and deep traps spectra of a-plane GaN films grown on r-plane sapphire. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2010</b> , 166, 220-224	3.1	22
29	A conductivity-based selective etching for next generation GaN devices. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1713-1716	1.3	68
28	Effect of gate orientation on dc characteristics of Si-doped, nonpolar AlGaIn/GaN metal-oxide semiconductor high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 082110	3.4	11
27	Improving microstructural quality of semipolar (11̄2 2) GaN on m-plane sapphire by a two-step growth process. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 231904	3.4	62
26	Improved hydrogen detection sensitivity in N-polar GaN Schottky diodes. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 212108	3.4	48
25	High sensitivity of hydrogen sensing through N-polar GaN Schottky diodes. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1202, 178		

24	Effect of Controlled Growth Dynamics on the Microstructure of Nonpolar a-Plane GaN Revealed by X-ray Diffraction. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 071002	1.4	35
23	Morphological and microstructural evolution in the two-step growth of nonpolar a-plane GaN on r-plane sapphire. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 123519	2.5	67
22	Nitride-organic hybrid heterostructures for possible novel optoelectronic devices: charge injection and transport. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, 593-595		7
21	Hydrogen sensing of N-polar and Ga-polar GaN Schottky diodes. <i>Sensors and Actuators B: Chemical</i> , <b>2009</b> , 142, 175-178	8.5	20
20	N-face GaN growth on c-plane sapphire by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 2948-2952	1.6	44
19	Effect of NH <sub>3</sub> flow rate on m-plane GaN growth on m-plane SiC by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 3824-3829	1.6	16
18	Microstructural evolution in m-plane GaN growth on m-plane SiC. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 051112	3.4	28
17	Nitrogen-polar GaN growth evolution on c-plane sapphire. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 131912	3.4	57
16	Understanding nonpolar GaN growth through kinetic Wulff plots. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 093523	2.5	85
15	High-temperature AlN interlayer for crack-free AlGa <sub>N</sub> growth on GaN. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 043516	2.5	8
14	Reduction of stacking fault density in m-plane GaN grown on SiC. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 111904	3.4	48
13	UV LED arrays at 280 and 340 nm for spectroscopic biosensing. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2007</b> , 204, 2112-2116	1.6	8
12	Depth dependence of structural quality in InN grown by metalorganic chemical vapor deposition. <i>Materials Letters</i> , <b>2007</b> , 61, 516-519	3.3	3
11	Observation of oxide precipitates in InN nanostructures. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 234102	3.4	6
10	Heteroepitaxy of AlGa <sub>N</sub> on bulk AlN substrates for deep ultraviolet light emitting diodes. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 051116	3.4	70
9	Spatial distribution of deep level defects in crack-free AlGa <sub>N</sub> grown on GaN with a high-temperature AlN interlayer. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 123101	2.5	11
8	Effects of grain size on the mosaic tilt and twist in InN films grown on GaN by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 092114	3.4	11
7	Influence of cracks generation on the structural and optical properties of GaN/Al <sub>0.55</sub> Ga <sub>0.45</sub> N multiple quantum wells. <i>Applied Surface Science</i> , <b>2006</b> , 252, 3043-3050	6.7	1



6	Evolution of mosaic structure in InN grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2006</b> , 293, 269-272	1.6	8
5	Influence of dislocations on photoluminescence of InGaN/GaN multiple quantum wells. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 071908	3-4	46
4	Low-temperature growth of InN by MOCVD and its characterization. <i>Journal of Crystal Growth</i> , <b>2005</b> , 276, 13-18	1.6	29
3	Study on the thermal stability of InN by in-situ laser reflectance system. <i>Journal of Crystal Growth</i> , <b>2005</b> , 281, 310-317	1.6	10
2	Lateral phase separation in AlGaIn grown on GaN with a high-temperature AlN interlayer. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 121914	3-4	27
1	One-step hydrothermal process to prepare highly crystalline Fe <sub>3</sub> O <sub>4</sub> nanoparticles with improved magnetic properties. <i>Materials Research Bulletin</i> , <b>2003</b> , 38, 1113-1118	5.1	161